

Block Course "GaAs Fabrication"

Plasma Etch Parameters

Base Pressure: 5e-5 mbar
Gas: 16% O₂, 250 mTorr
Power: 30 W
Time: 40 s

Ohmic Contacts: Annealing Recipe

Step Nr.	Temperatures/°C	Time/s	Type
1	100	60	1 (vacuum)
2	100	60	3 (gas flow)
3	100	60	1 (vacuum)
4	370	120	2 (forming gas)
5	440-500	60	2 (forming gas)
6	100	60	3 (gas flow)

Gas used: Forming gas (H₂ and N₂)

Au wire bonding

standard chip carrier:

	Search	Power	time	force
1 st	0.5	3.2	4.7	2.9
2 nd	0.5	1.9	5.1	3

loop	2.3-3.5
tail	1.5
tear	3.3